

Docket No.: 2009211US0



#8/A
3-17-03
G. Antai

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
Yukihiko SHIRAKAWA :
SERIAL NO: 09/866,732 :
FILED: May 30, 2001 :
FOR: THIN-FILM EL DEVICE, AND ITS FABRICATION PROCESS

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits please amend the above-identified application as follows.

IN THE SPECIFICATION

Please amend the specification as follows:

Page 10, line 18 and 25, please replace the paragraph with the following paragraph:

A1
The lower electrode layer should preferably be formed of a material which ensures high electrical conductivity, receives no damage during dielectric layer formation, and has a low reactivity with respect to the dielectric layer or light-emitting layer. Desired for such a lower electrode layer material are noble metals such as Au, Pt, Pd, Ir and Ag, noble metal alloys such as Au-Pd, Au-Pt, Ag-Pd, and Ag-Pt, and electrode materials composed mainly of noble metals such as Ag-Pd-Cu with base metal elements added thereto, because oxidation resistance with respect to an oxidizing atmosphere used for the firing of the dielectric layer material can be easily obtained. Use may also be made of oxide conductive materials such as